

NVLUD4C26N

MOSFET – Power, Dual, N-Channel, μ Cool, 2.0x2.0x0.55 mm, UDFN6 30 V, 7.3 A



ON Semiconductor®

www.onsemi.com

Features

- UDFN Package with Exposed Drain Pads for Excellent Thermal Conduction
- Low Profile UDFN 2.0 x 2.0 x 0.55 mm for Board Space Saving
- Ultra Low $R_{DS(on)}$
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Power Load Switch
- Wireless Charging
- DC-DC Converters

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

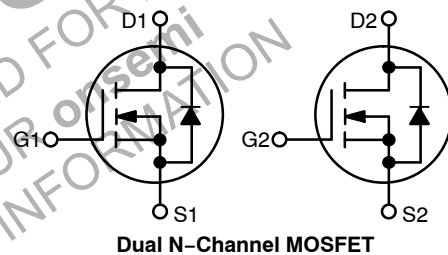
Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	30	V
Gate-to-Source Voltage			V_{GS}	± 12	V
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	7.3	A
		$T_A = 85^{\circ}\text{C}$		5.3	
	$t \leq 5\text{ s}$	$T_A = 25^{\circ}\text{C}$		9.1	
Power Dissipation (Note 1)	Steady State	$T_A = 25^{\circ}\text{C}$	P_D	1.70	W
		$t \leq 5\text{ s}$		$T_A = 25^{\circ}\text{C}$	
Continuous Drain Current (Note 2)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	4.8	A
		$T_A = 85^{\circ}\text{C}$		3.4	
Power Dissipation (Note 2)		$T_A = 25^{\circ}\text{C}$	P_D	0.72	W
Pulsed Drain Current		$t_p = 10\text{ }\mu\text{s}$	I_{DM}	22	A
MOSFET Operating Junction and Storage Temperature			T_J , T_{STG}	-55 to 150	$^{\circ}\text{C}$
Source Current (Body Diode) (Note 1)			I_S	3.0	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^{\circ}\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
2. Surface-mounted on FR4 board using the minimum recommended pad size, 2 oz. Cu.

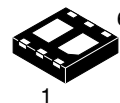
MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
30 V	21 m Ω @ 10 V	7.3 A
	24 m Ω @ 4.5 V	
	26 m Ω @ 3.7 V	
	28 m Ω @ 3.3 V	
	36 m Ω @ 2.5 V	
	65 m Ω @ 1.8 V	

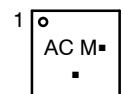


Dual N-Channel MOSFET

MARKING DIAGRAM

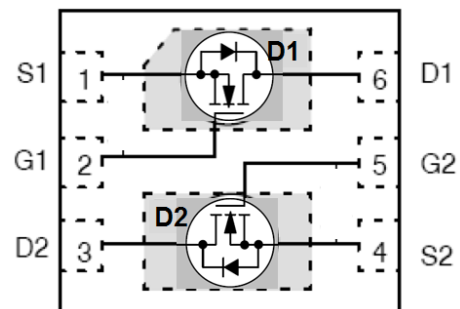


UDFN6
CASE 517BF
 μ COOL™



AC = Specific Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)



(Top View)

ORDERING INFORMATION

See detailed ordering and shipping information on page 3 of this data sheet.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	73.6	°C/W
Junction-to-Ambient – $t \leq 5$ s (Note 3)	$R_{\theta JA}$	47.6	
Junction-to-Ambient – Steady State min Pad (Note 4)	$R_{\theta JA}$	174.4	

3. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
 4. Surface-mounted on FR4 board using the minimum recommended pad size, 2 oz. Cu.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
-----------	--------	----------------	-----	-----	-----	-------

OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 250\text{ }\mu\text{A}$, ref to 25°C		7		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 24\text{ V}$	$T_J = 25^\circ\text{C}$		1	μA
			$T_J = 125^\circ\text{C}$		10	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	0.6		1.1	V
Negative Threshold Temp. Coefficient	$V_{GS(TH)}/T_J$			2.8		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 6.0\text{ A}$		17.5	21	m Ω
		$V_{GS} = 4.5\text{ V}, I_D = 5.0\text{ A}$		20	24	
		$V_{GS} = 3.7\text{ V}, I_D = 3.0\text{ A}$		21	26	
		$V_{GS} = 3.3\text{ V}, I_D = 3.0\text{ A}$		22	28	
		$V_{GS} = 2.5\text{ V}, I_D = 2.0\text{ A}$		25	36	
		$V_{GS} = 1.8\text{ V}, I_D = 1.0\text{ A}$		40	65	
Forward Transconductance	g_{FS}	$V_{DS} = 1.5\text{ V}, I_D = 5.0\text{ A}$		23		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 15\text{ V}$		460		pF
Output Capacitance	C_{OSS}			225		
Reverse Transfer Capacitance	C_{RSS}			27		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 10\text{ V}; I_D = 5.0\text{ A}$		5.0	8.0	nC
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}; I_D = 5.0\text{ A}$		5.5	9.0	nC
Threshold Gate Charge	$Q_{G(TH)}$			0.55		
Gate-to-Source Charge	Q_{GS}			2.5		
Gate-to-Drain Charge	Q_{GD}			1.1		

SWITCHING CHARACTERISTICS, $V_{GS} = 4.5\text{ V}$ (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DD} = 15\text{ V}, I_D = 5.0\text{ A}, R_G = 1\text{ }\Omega$		5		ns
Rise Time	t_r			15		
Turn-Off Delay Time	$t_{d(OFF)}$			13		
Fall Time	t_f			1.7		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 6. Switching characteristics are independent of operating junction temperatures.

NVLUD4C26N

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
DRAIN-SOURCE DIODE CHARACTERISTICS						
Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}$, $I_S = 2.0\text{ A}$				
		$T_J = 25^\circ\text{C}$		0.7	1.0	V
		$T_J = 125^\circ\text{C}$		0.6		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}$, $dI_S/dt = 100\text{ A}/\mu\text{s}$, $I_S = 2.0\text{ A}$		18.5		ns
Charge Time	t_a			9.3		
Discharge Time	t_b			9.1		
Reverse Recovery Charge	Q_{RR}			7.8		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

6. Switching characteristics are independent of operating junction temperatures.

DEVICE ORDERING INFORMATION

Device	Package	Shipping†
NVLUD4C26NTAG	UDFN6 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

DISCONTINUED
THIS DEVICE IS NOT RECOMMENDED FOR NEW DESIGN
PLEASE CONTACT YOUR onsemi
REPRESENTATIVE FOR INFORMATION

TYPICAL CHARACTERISTICS

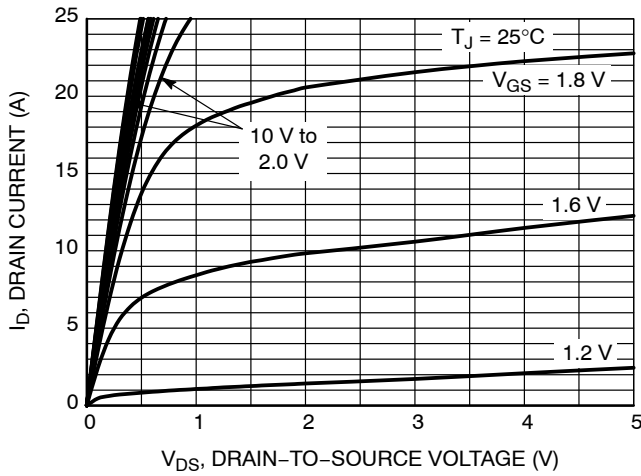


Figure 1. On-Region Characteristics

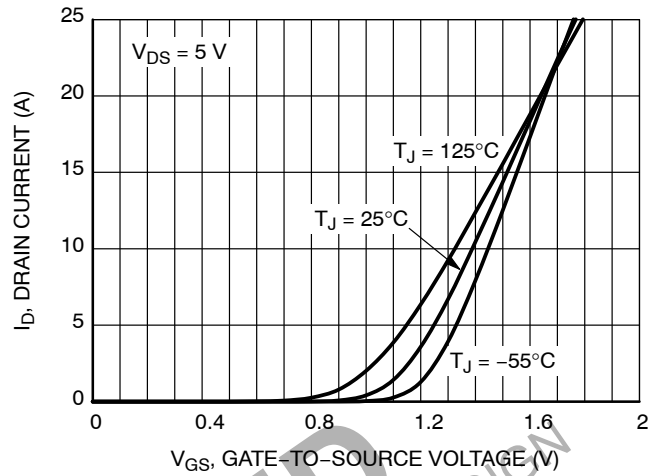


Figure 2. Transfer Characteristics

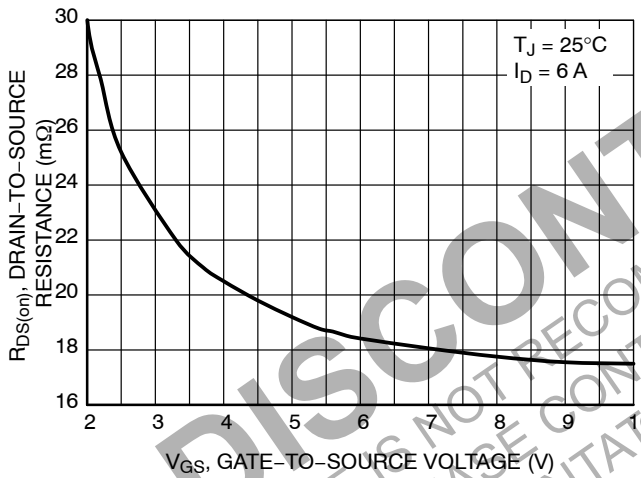


Figure 3. On-Resistance vs. Gate-to-Source Voltage

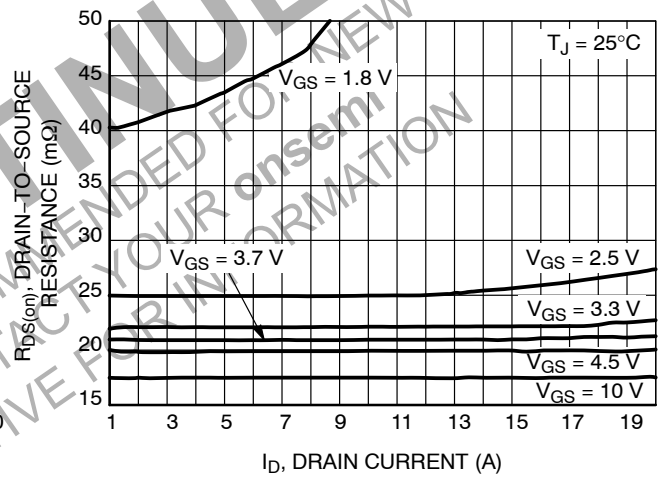


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

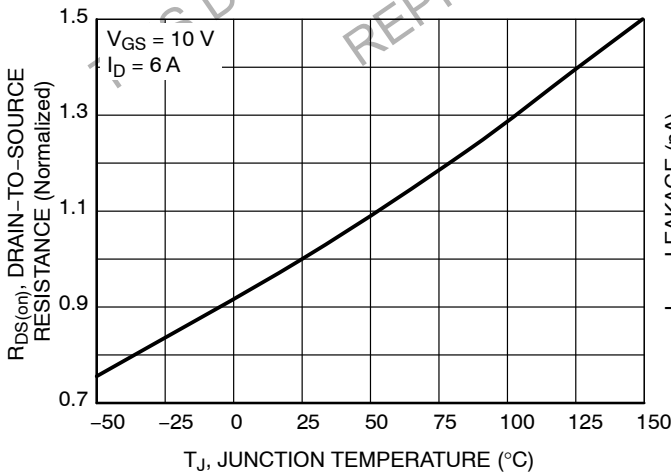


Figure 5. On-Resistance Variation with Temperature

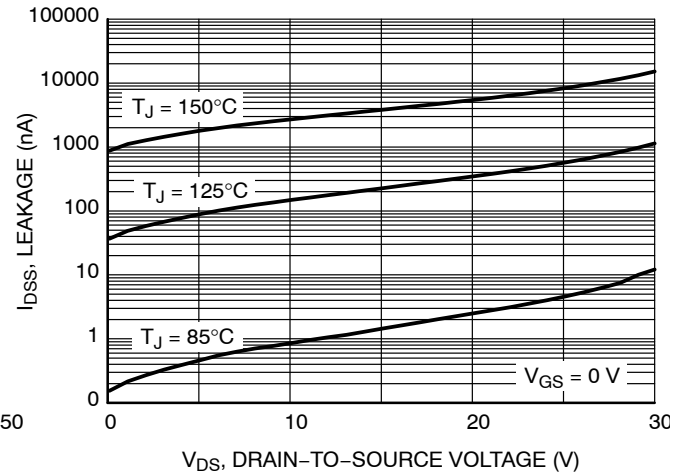


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

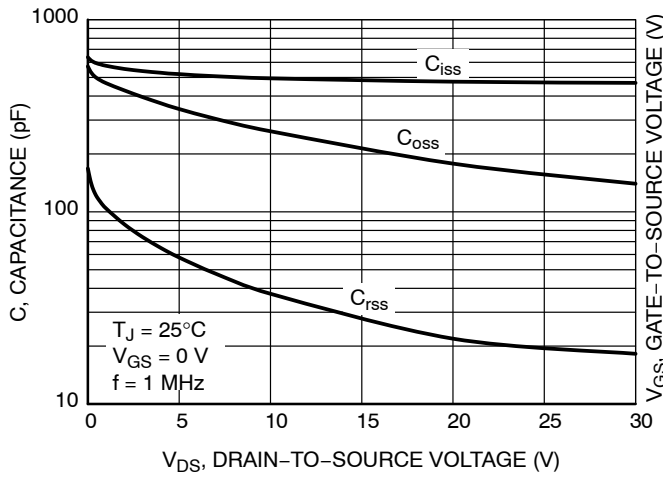


Figure 7. Capacitance Variation

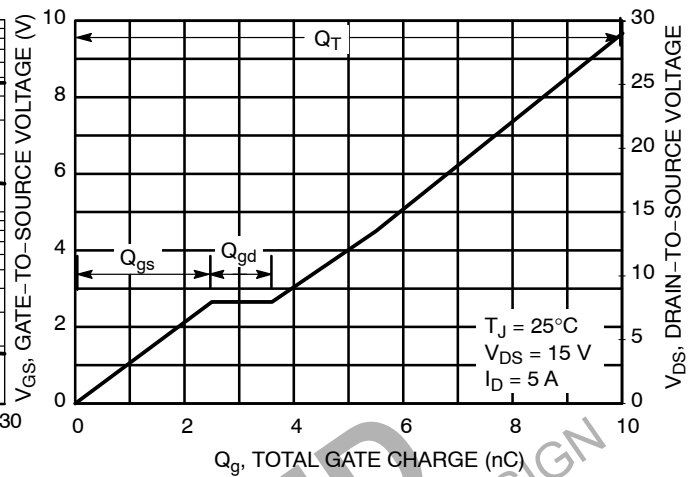


Figure 8. Gate-to-Source vs. Total Charge

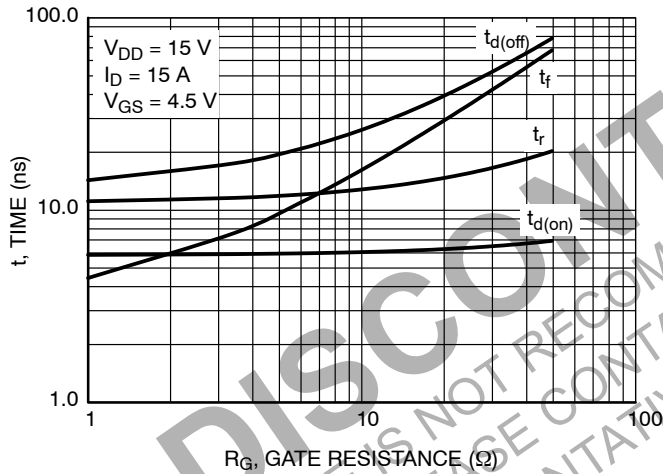


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

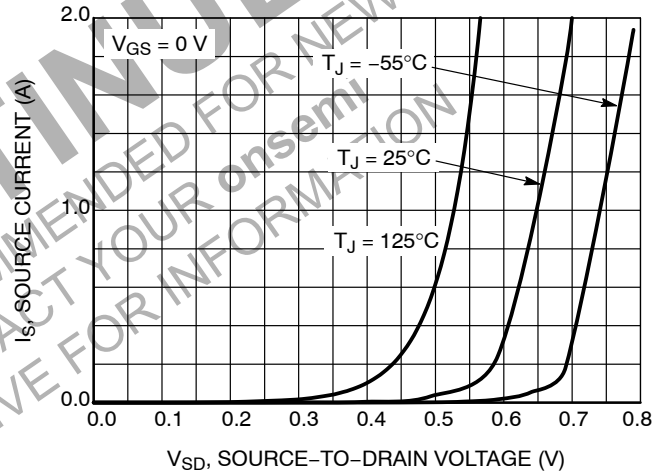


Figure 10. Diode Forward Voltage vs. Current

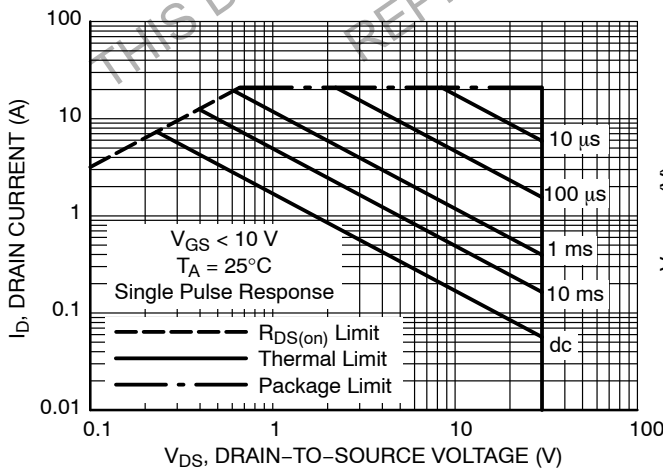


Figure 11. Maximum Rated Forward Biased Safe Operating Area

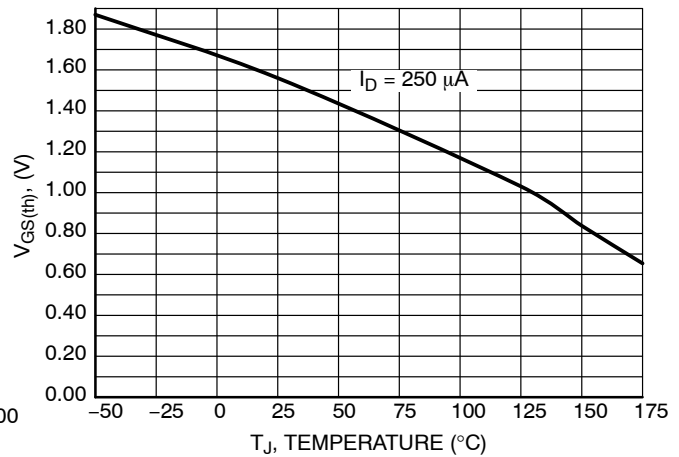


Figure 12. Threshold Voltage

TYPICAL CHARACTERISTICS

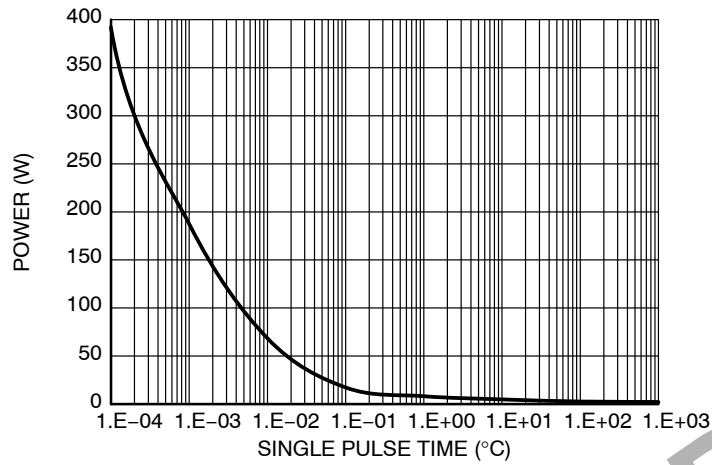


Figure 13. Single Pulse Maximum Power Dissipation

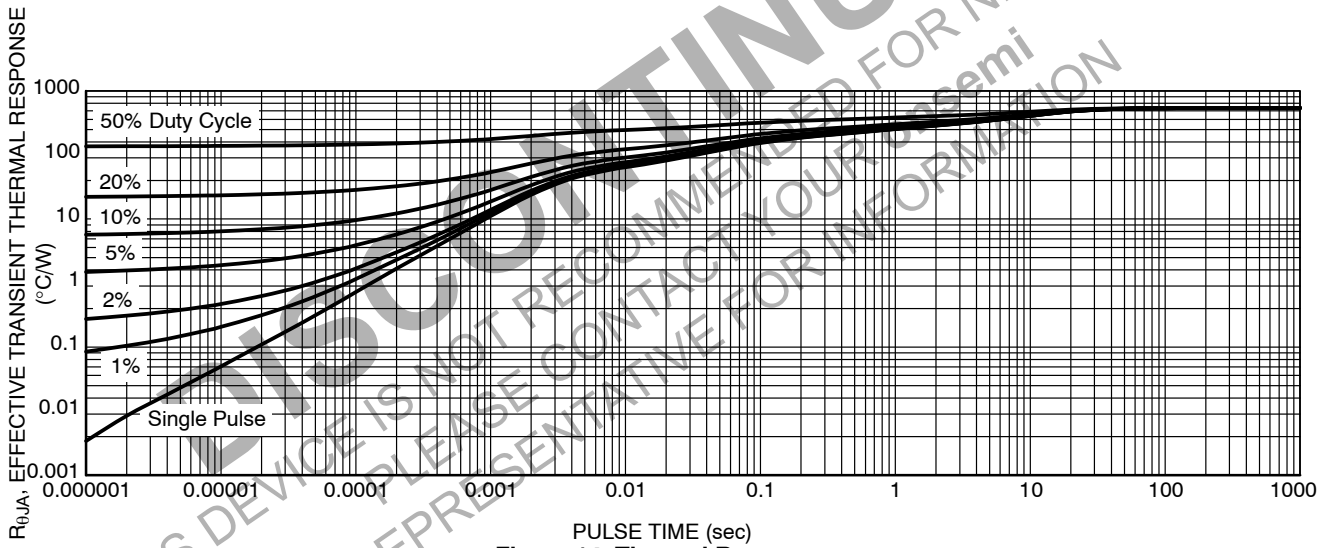
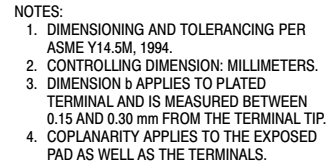


Figure 14. Thermal Response



DATE 20 AUG 2012



DIM	MILLIMETERS	
	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A3	0.13 REF	
b	0.25	0.35
D	2.00 BSC	
D2	0.57	0.77
E	2.00 BSC	
E2	0.90	1.10
e	0.65 BSC	
F	0.15 BSC	
K	0.25 REF	
L	0.20	0.30
L1	0.10	

1

M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98AON48159E	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	UDFN6 2x2, 0.65P	PAGE 1 OF 1

www.onsemi.com

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at
www.onsemi.com/support/sales